

Figure 1. Pin Assignment (Top View)

	PIN ASSIGNMENT						
1	IN A1						
2	IN B1						
3	OUT Y1						
4	IN A2						
5	IN B2						
6	OUT Y2						
7	GND						
8	OUT \overline{Y3}						
9	IN A3						
10	IN B3						
11	OUT Y4						
12	IN A4						
13	IN B4						
14	V <sub>CC</sub>						

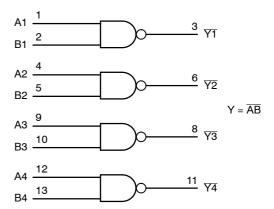


Figure 2. Logic Diagram

# **FUNCTION TABLE**

Inp	uts	Output	
Α	В	Y	
L	L	Н	
L	Н	Н	
Н	L	Н	
Н	Н	L	

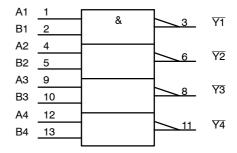


Figure 3. IEC LOGIC DIAGRAM

#### **MAXIMUM RATINGS** (Note 1)

Symbol	Ch	aracteristics	Value	Unit
V <sub>CC</sub>	DC Supply Voltage		-0.5 to +7.0	V
V <sub>IN</sub>	DC Input Voltage		-0.5 to +7.0	V
V <sub>OUT</sub>	DC Output Voltage	V <sub>CC</sub> = 0 High or Low State	-0.5 to 7.0 -0.5 to V <sub>CC</sub> + 0.5	٧
I <sub>IK</sub>	Input Diode Current		-20	mA
lok	Output Diode Current	$V_{OUT} < GND; V_{OUT} > V_{CC}$	+20	mA
lout	DC Output Current, per Pin		+25	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and	+50	mA	
P <sub>D</sub>	Power Dissipation in Still Air,	SOIC Package (Note 2) TSSOP Package (Note 2)	500 450	mW
TL	Lead temperature, 1 mm from	n case for 10 s	260	°C
T <sub>stg</sub>	Storage temperature		-65 to +150	°C
V <sub>ESD</sub>	ESD Withstand Voltage	Human Body Model (Note 3) Machine Model (Note 4) Charged Device Model (Note 5)	> 2000 > 200 > 3000	٧
I <sub>Latch-Up</sub>	Latch-Up Performance (Note 6)	Above V <sub>CC</sub> and Below GND at 125°C	±300	mA

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, Vin and Vout should be constrained to the range GND  $\leq$  (V<sub>in</sub> or  $V_{out}$ )  $\leq V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V<sub>CC</sub>). Unused outputs must be left

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- \* Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied.
- 1. Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.
- 2. Derating -
- SOIC Package: -7 mW/°C from 65° to 125°C
   TSSOP Package: -6.1 mW/°C from 65° to 125°C
- 3. Tested to EIA/JESD22-A114-A
- 4. Tested to EIA/JESD22-A115-A
- 5. Tested to JESD22-C101-A
- 6. Tested to EIA/JESD78

#### RECOMMENDED OPERATING CONDITIONS

Symbol	Charact	Min	Max	Unit	
V <sub>CC</sub>	DC Supply Voltage		3.0	5.5	V
V <sub>IN</sub>	DC Input Voltage	0.0	5.5	V	
V <sub>OUT</sub>	DC Output Voltage	VCC = 0 High or Low State	0.0 0.0	5.5 V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature Range		-55	+125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0 0	100 20	ns/V

The  $\theta_{JA}$  of the package is equal to 1/Derating. Higher junction temperatures may affect the expected lifetime of the device per the table and figure below.

# DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

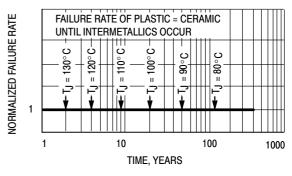


Figure 4. Failure Rate vs. Time Junction Temperature

# DC ELECTRICAL CHARACTERISTICS

			V <sub>CC</sub>	7	T <sub>A</sub> = 25°C		T <sub>A</sub> ≤ 85°C T		<b>T</b> <sub>A</sub> ≤ 1	T <sub>A</sub> ≤ 125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage		3.0 4.5 5.5	1.4 2.0 2.0			1.4 2.0 2.0		1.4 2.0 2.0		٧
V <sub>IL</sub>	Maximum Low-Level Input Voltage		3.0 4.5 5.5			0.53 0.8 0.8		0.53 0.8 0.8		0.53 0.8 0.8	<b>V</b>
V <sub>OH</sub>	Minimum High-Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50  \mu\text{A}$	3.0 4.5	2.9 4.4	3.0 4.5		2.9 4.4		2.9 4.4		V
	$V_{IN} = V_{IH}$ or $V_{IL}$	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -4 \text{ mA}$ $I_{OH} = -8 \text{ mA}$	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		<b>V</b>
V <sub>OL</sub>	Maximum Low-Level Output Voltage V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$V_{IN} = V_{IH}$ or $V_{IL}$ $I_{OL} = 50 \mu A$	3.0 4.5		0.0 0.0	0.1 0.1		0.1 0.1		0.1 0.1	V
		V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OL</sub> = 4 mA I <sub>OL</sub> = 8 mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	٧
I <sub>IN</sub>	Maximum Input Leakage Current	V <sub>IN</sub> = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μА
I <sub>CC</sub>	Maximum Quiescent Supply Current	V <sub>IN</sub> = V <sub>CC</sub> or GND	5.5			2.0		20		40	μΑ
I <sub>CCT</sub>	Quiescent Supply Current	Input: V <sub>IN</sub> = 3.4 V	5.5			1.35		1.50		1.65	mA
I <sub>OPD</sub>	Output Leakage Current	V <sub>OUT</sub> = 5.5 V	0.0			0.5		5.0		10	μΑ

# AC ELECTRICAL CHARACTERISTICS $C_{load}$ = 50 pF, Input $t_{r}$ = $t_{f}$ = 3.0 ns

				T <sub>A</sub> = 25°C		T <sub>A</sub> = 25°C		<b>T</b> <sub>A</sub> ≤ 85°C <b>T</b> <sub>A</sub>		T <sub>A</sub> ≤ 125°C	
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Min	Max	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propogation Delay, Input A or B to Y	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		4.1 5.5	10.0 13.5		11.0 15.0		13.0 17.5	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		3.1 3.6	6.9 7.9		8.0 9.0		9.5 10.5	
C <sub>IN</sub>	Maximum Input Capacitance				5.5	10		10		10	pF

		Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
$C_{PD}$	Power Dissipation Capacitance (Note 7)	17	pF

<sup>7.</sup> C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>. C<sub>PD</sub> is used to determine the no–load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

# $\textbf{NOISE CHARACTERISTICS} \text{ (Input } t_{\text{r}} = t_{\text{f}} = 3.0 \text{ns, } C_{\text{L}} = 50 \text{pF, } V_{\text{CC}} = 5.0 \text{V, Measured in SO Package)}$

		T <sub>A</sub> = 25°C		
Symbol	Characteristic		Max	Unit
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>	0.4	0.8	V
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>	- 0.4	- 0.8	V
V <sub>IHD</sub>	Minimum High Level Dynamic Input Voltage		2.0	V
$V_{ILD}$	Maximum Low Level Dynamic Input Voltage		0.8	V

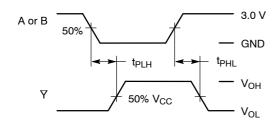
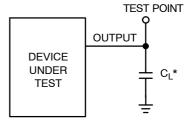


Figure 5. Switching Waveforms



\*Includes all probe and jig capacitance

Figure 6. Test Circuit

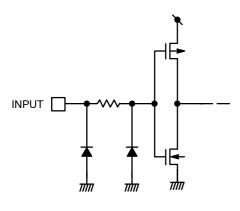


Figure 7. Input Equivalent Circuit

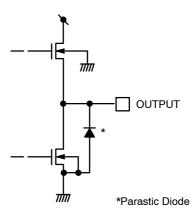


Figure 8. Output Equivalent Circuit

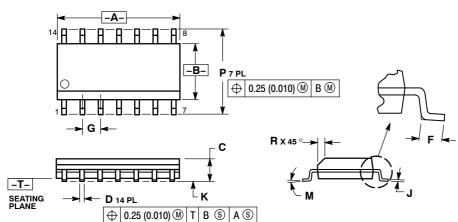
# **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74VHCT00AD	SOIC-14	48 Units / Rail
MC74VHCT00ADR2	SOIC-14	2500 / Tape & Reel
MC74VHCT00ADR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel
MC74VHCT00ADT	TSSOP-14	96 Units / Rail
MC74VHCT00ADTR2	TSSOP-14	2000 / Tape & Reel
MC74VHCT00ADTR2G	TSSOP-14 (Pb-Free)	2000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

## **PACKAGE DIMENSIONS**

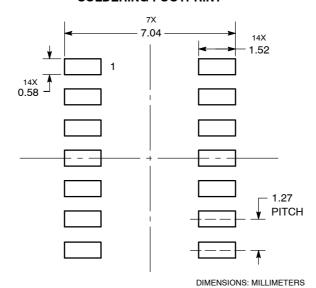
# SOIC-14 **D SUFFIX** CASE 751A-03 **ISSUE J**



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
  4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) DER SIDE
- 4. MAXIMUM MOLD PROTRUSION 0.15 (0.00 PER SIDE.
  5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

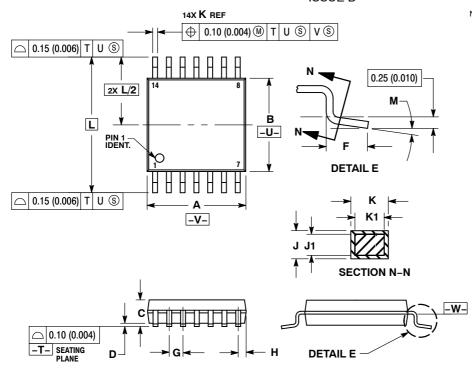
	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
М	0 °	7°	0 °	7°
Р	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

#### **SOLDERING FOOTPRINT**



#### PACKAGE DIMENSIONS

# TSSOP-14 **DT SUFFIX** CASE 948G-01 **ISSUE B**



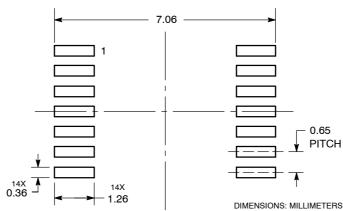
#### NOTES

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.
- 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT
- EXCEED 0.15 (0.006) PER SIDE.
  4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL
- NOT EXCEED 0.25 (0.010) PER SIDE. 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

  7. DIMENSION A AND B ARE TO BE
  DETERMINED AT DATUM PLANE —W

PETE	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026	BSC	
Н	0.50	0.60	0.020	0.024	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
Ĺ	6.40		0.252 BSC		
М	0 °	8 °	0 °	8 °	

#### **SOLDERING FOOTPRINT**



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